

TRANSISTOR MODULE (Hi-β)

SQD300BA60



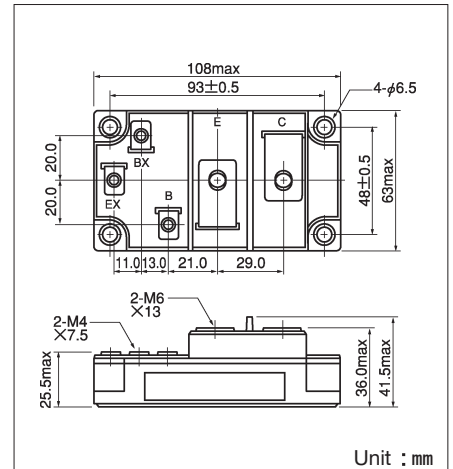
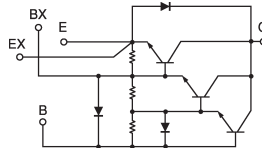
UL;E76102 (M)

SQD300BA60 is a Darlington power transistor module with a **ULTRA HIGH** h_{FE} , high speed, high power Darlington transistor. The transistor has a reverse paralleled fast recovery diode (t_{rr} : 200ns). The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction,

- $I_C=300A$, $V_{CEX}=600V$
- Low saturation voltage for higher efficiency.
- ULTRA HIGH DC current gain h_{FE} . $h_{FE} \geq 750$
- Isolated mounting base
- V_{EBO} 10V for faster switching speed.

(Applications)

Motor Control (VVF), AC/DC Servo, UPS, Switching Power Supply, Ultrasonic Application



Maximum Ratings

($T_j=25^\circ C$)

Symbol	Item	Conditions	Ratings		Unit
			SQD300BA60		
V_{CBO}	Collector-Base Voltage		600		V
V_{CEX}	Collector-Emmitter Voltage	$V_{BE} = -2V$	600		V
V_{EBO}	Emmitter-Base Voltage		10		V
I_C	Collector Current	() =pw≤1ms	300 (600)		A
$-I_C$	Reverse Collector Current		300		A
I_B	Base Current		18		A
P_T	Total power dissipation	$T_C=25^\circ C$	1380		W
T_j	Junction Temperature		-40~+150		$^\circ C$
T_{stg}	Storage Temperature		-40~+125		$^\circ C$
V_{ISO}	Isolation Voltage	A.C.1minute	2500		V
	Mounting Torque	(M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	
		Terminal (M4)	Recommended Value 1.0~1.4 (10~14)	1.5 (15)	
	Mass	Typical Value	460		g

Electrical Characteristics

($T_j=25^\circ C$)

Symbol	Item	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
I_{CBO}	Collector Cut-off Current	$V_{CB} = V_{CBO}$			4.0	mA
I_{EBO}	Emmitter Cut-off Current	$V_{EB} = V_{EBO}$			1200	mA
$V_{CEO(SUS)}$	Collector Emmitter Sustaning Voltage	$I_C=1A$	450			V
$V_{CEX(SUS)}$		$I_C=60A, I_{B2} = -10A$	600			
h_{FE}	DC Current Gain	$I_C=300A, V_{CE}=2.5V$	750			
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage	$I_C=300A, I_B=400mA$			2.5	V
$V_{BE(sat)}$	Base-Emmitter Saturation Voltage	$I_C=300A, I_B=400mA$			3.0	V
t_{on}	Switching Time	On Time			2.0	μs
t_s		Storage Time	$V_{CC}=300V, I_C=300A$		8.0	
t_f		Fall Time	$I_{B1}=0.6A, I_{B2}=-6A$		2.0	
V_{ECO}	Collector-Emmitter Reverse Voltage	$I_C = -300A$			1.8	V
t_{rr}	Reverse Recovery time	$V_{CC}=300V, I_C = -300A, -di/dt=300A/\mu s, V_{BE} = -5V$		200		ns
$R_{th(j-c)}$	Thermal Impedance (junction to case)	Transistor part			0.09	$^\circ C/W$
		Diode part			0.3	

